

Load Switch with Level-Shift

PRODUCT SUMMARY		
V_{DS2} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
4.5 to 20	0.075 @ $V_{IN} = 10$ V	± 2.3
	0.120 @ $V_{IN} = 5.0$ V	± 1.9
	0.145 @ $V_{IN} = 4.5$ V	± 1.7

FEATURES

- 4.5-V Rated
- ESD Protected: 3000 V
- 105-m Ω Low $r_{DS(on)}$ TrenchFET[®]
- 4.5 to 20-V Input
- 1.5 to 8 -V Logic Level Control
- Low Profile, Small Footprint TSOP-6 Package
- 3000-V ESD Protection On Input Switch, $V_{ON/OFF}$
- Adjustable Slew-Rate



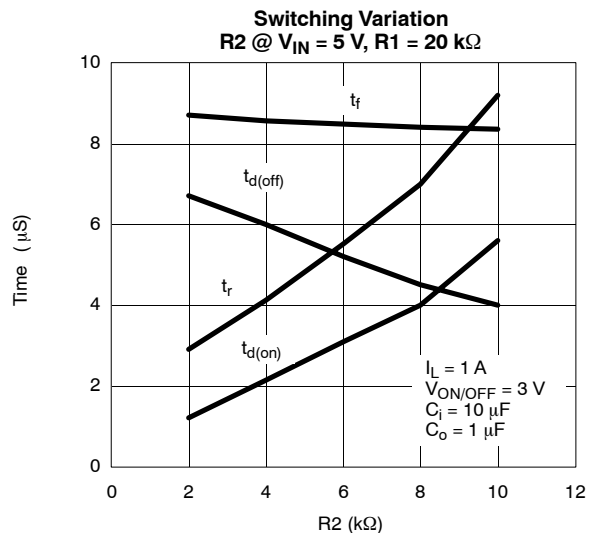
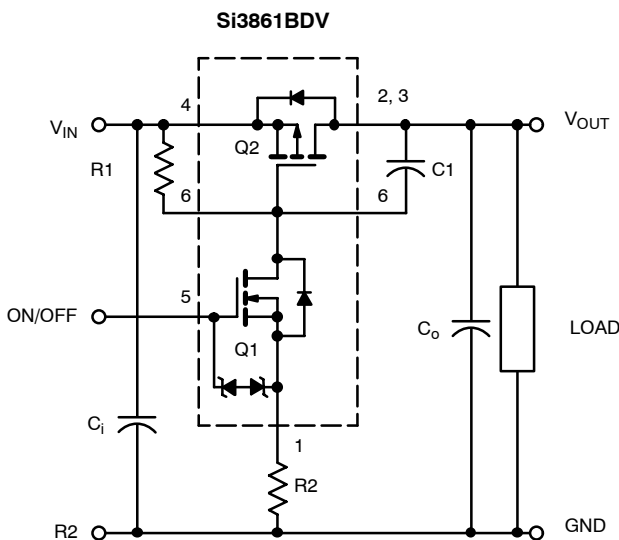
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COMPLIANT

DESCRIPTION

The Si3861BDV includes a p- and n-channel MOSFET in a single TSOP-6 package. The low on-resistance p-channel TrenchFET[®] is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a

level-shift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5-V. The Si3861BDV operates on supply lines from 4.5 to 20-V, and can drive loads up to 2.3 A.

APPLICATION CIRCUITS

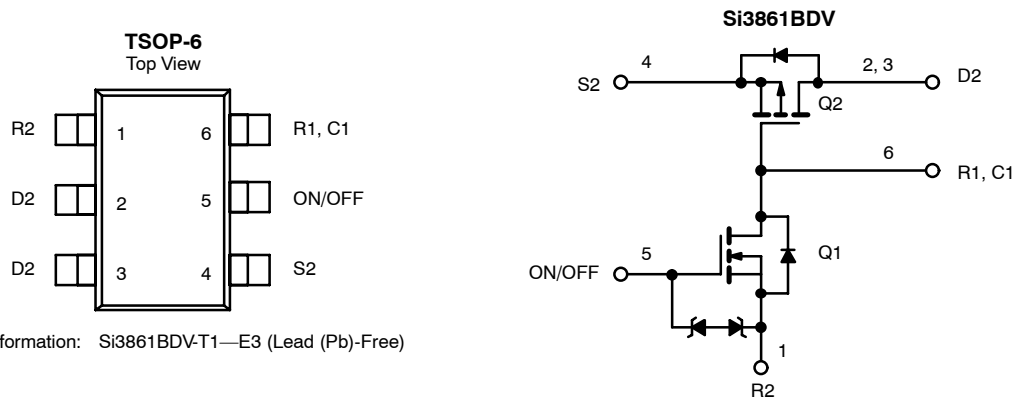


Note: For R2 switching variations with other $V_{IN}/R1$ combinations See Typical Characteristics

COMPONENTS		
R1	Pull-Up Resistor	Typical 10 k Ω to 1 m Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C1	Optional Slew-Rate Control	Typical 1000 pF

*Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

The Si3861BDV is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM


Ordering Information: Si3861BDV-T1—E3 (Lead (Pb)-Free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Input Voltage	V_{IN}	20	V
ON/OFF Voltage	$V_{ON/OFF}$	8	
Load Current	Continuous ^{a, b}	± 2.3	A
	Pulsed ^{b, c}	± 4	
Continuous Intrinsic Diode Conduction ^a	I_S	-1	
Maximum Power Dissipation ^a	P_D	0.83	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	3	kV

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (continuous current) ^a	R_{thJA}	120	150	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Foot (Q2)	R_{thJF}	60	80	

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
OFF Characteristics							
Reverse Leakage Current	I_{FL}	$V_{IN} = 30\text{ V}, V_{ON/OFF} = 0\text{ V}$			1	μA	
Diode Forward Voltage	V_{SD}	$I_S = -1\text{ A}$		-0.8	-1	V	
ON Characteristics							
Input Voltage Range	V_{IN}		4.5		20	V	
On-Resistance (p-channel) @ 1 A	$r_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}$ $I_D = 1\text{ A}$	$V_{IN} = 10\text{ V}$		0.060	0.075	Ω
			$V_{IN} = 5.0\text{ V}$		0.096	0.120	
			$V_{IN} = 4.5\text{ V}$		0.115	0.145	
On-State (p-channel) Drain-Current	$I_{D(on)}$	$V_{IN-OUT} \leq 0.2\text{ V}, V_{IN} = 10\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			A	
		$V_{IN-OUT} \leq 0.3\text{ V}, V_{IN} = 5\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1				

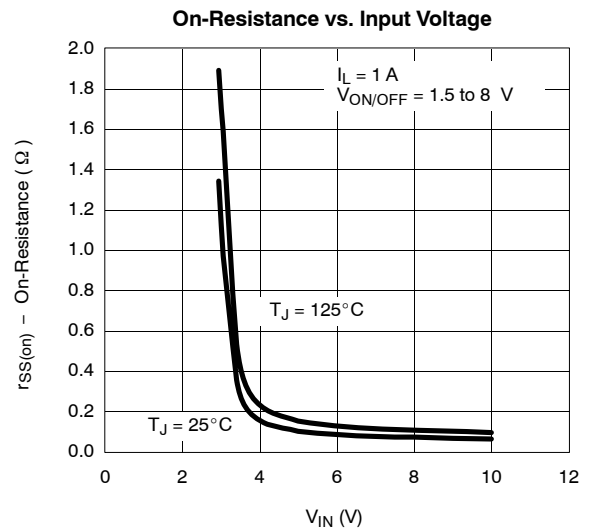
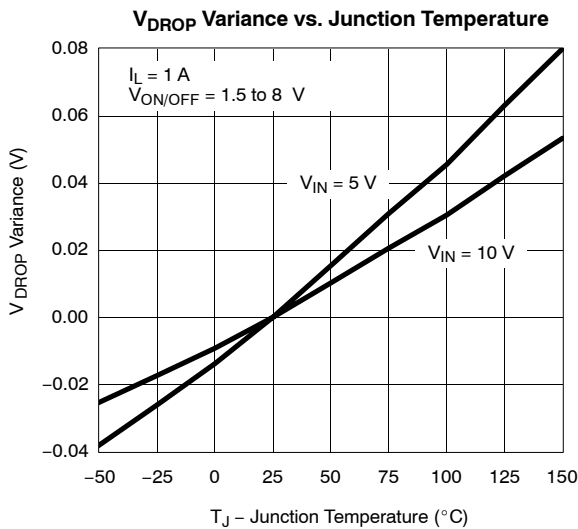
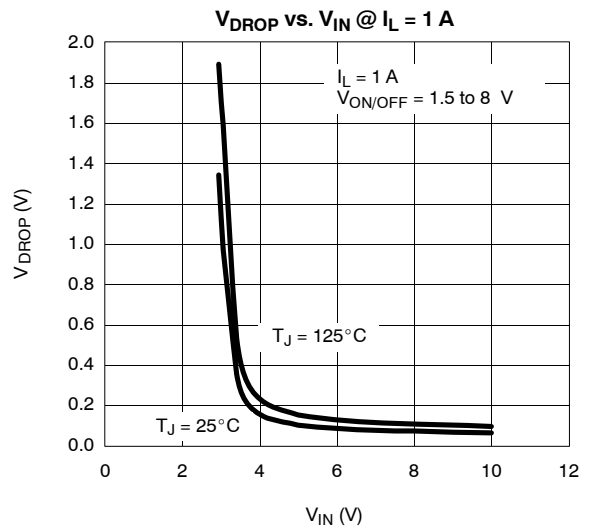
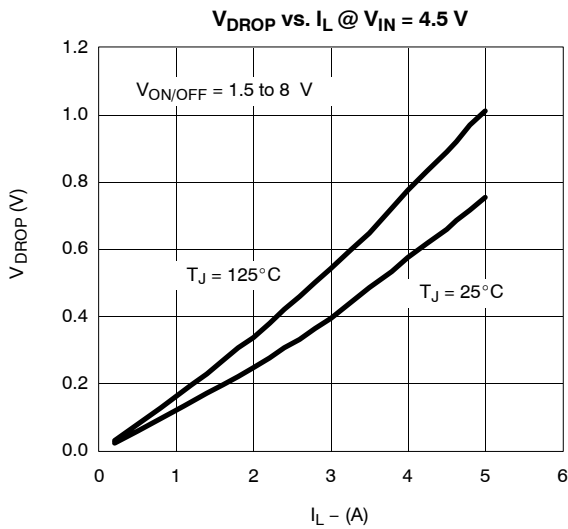
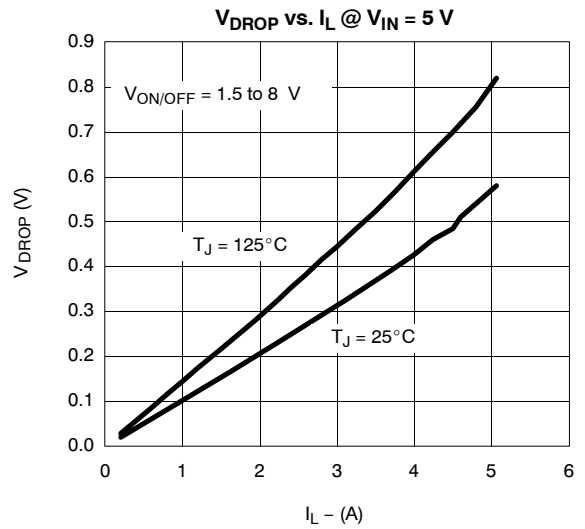
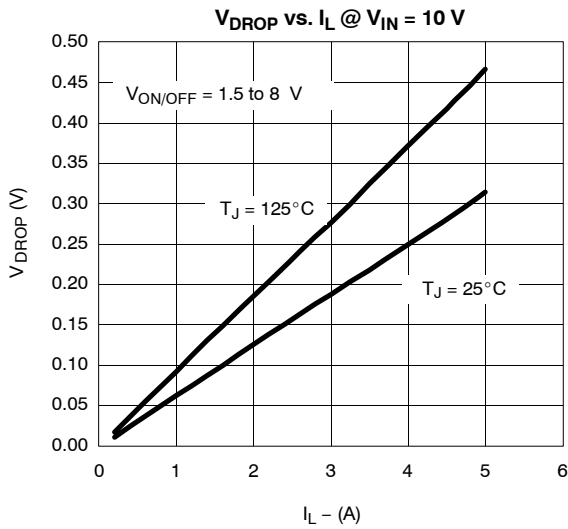
Notes

- Surface Mounted on FR4 Board.
- $V_{IN} = 12\text{ V}, V_{ON/OFF} = 8\text{ V}, T_A = 25^\circ\text{C}$.
- Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



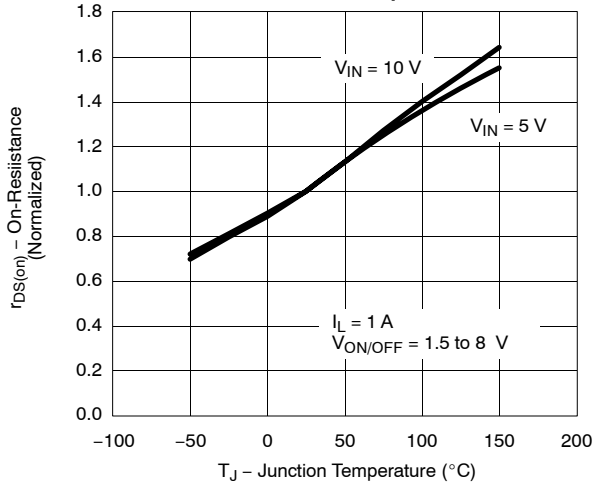
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



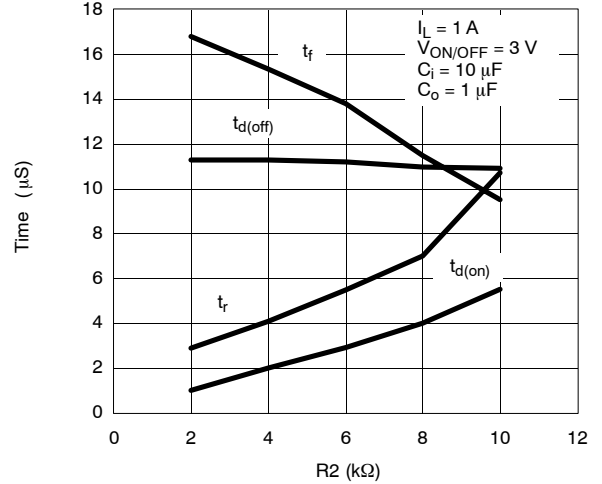


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

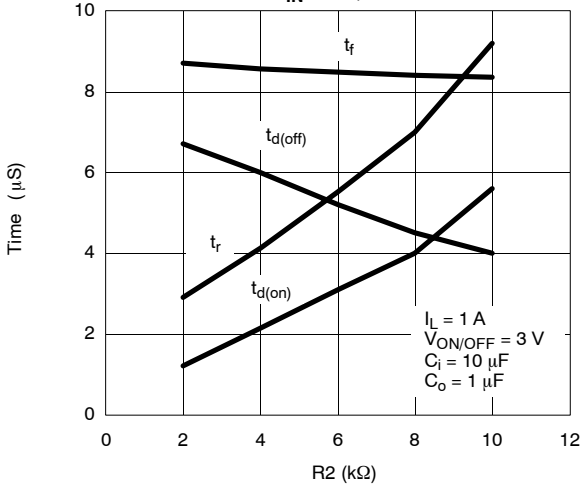
Normalized On-Resistance vs. Junction Temperature



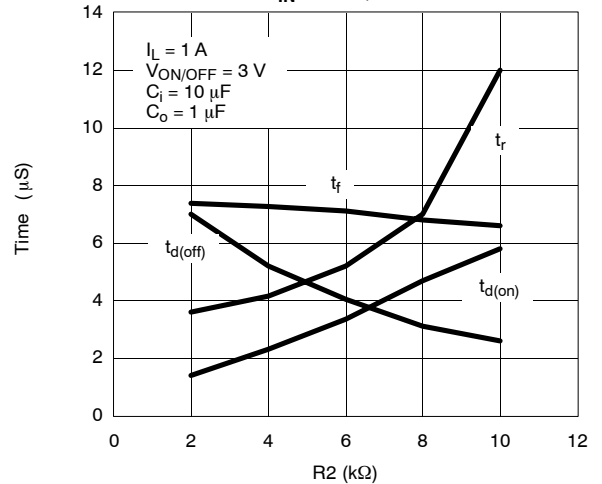
Switching Variation R2 @ V_IN = 10 V, R1 = 20 kΩ



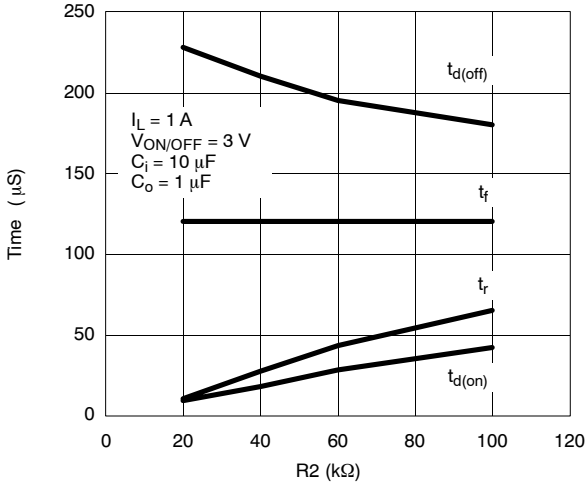
Switching Variation R2 @ V_IN = 5 V, R1 = 20 kΩ



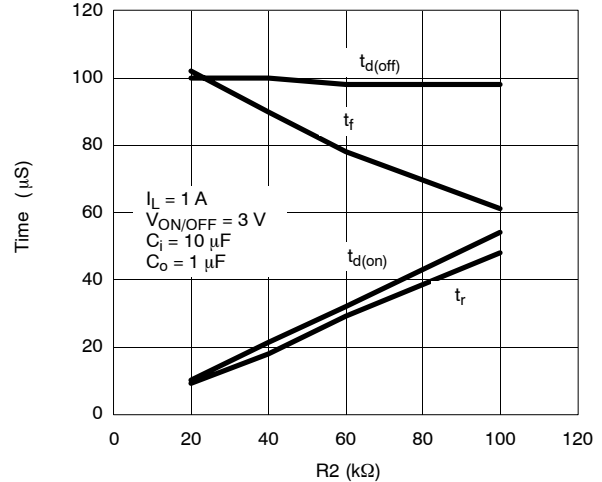
Switching Variation R2 @ V_IN = 4.5 V, R1 = 20 kΩ



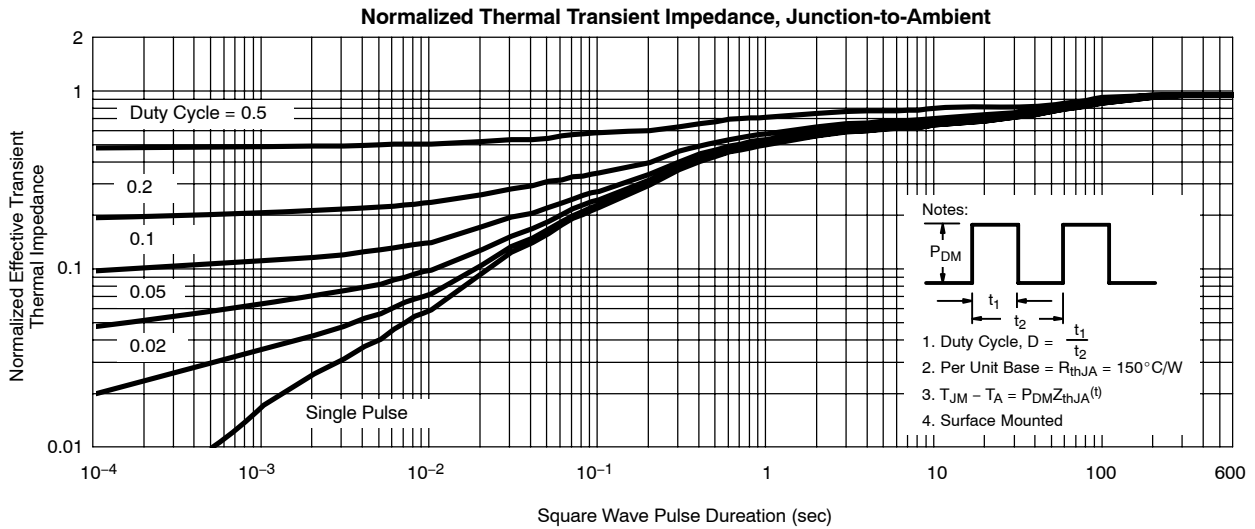
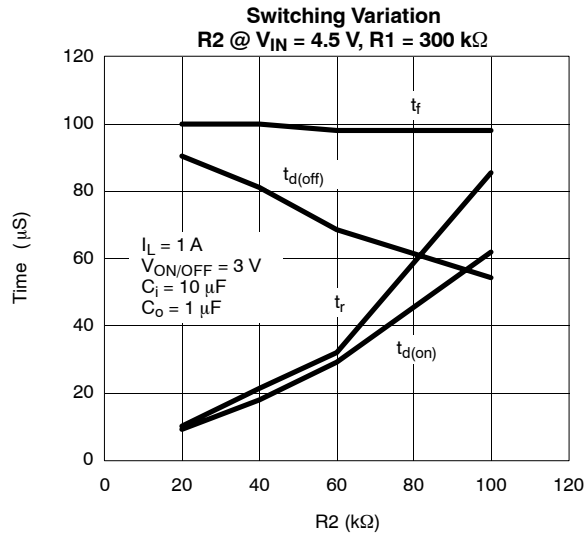
Switching Variation R2 @ V_IN = 10 V, R1 = 300 kΩ



Switching Variation R2 @ V_IN = 5 V, R1 = 300 kΩ



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



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